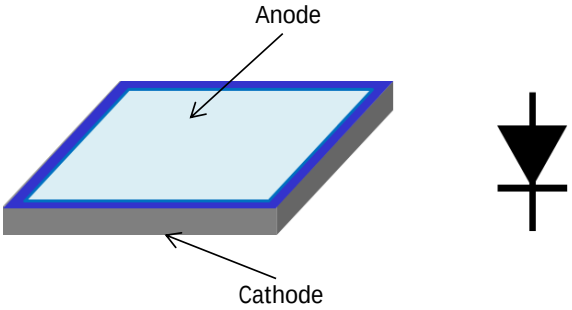
YJ Planar Fast Recovery Diode Die Specification

600V 15A, Fast recovery diode die based on silicon planar process
Part No.:LBDB5T600SS-330A

Main Products Characterstics



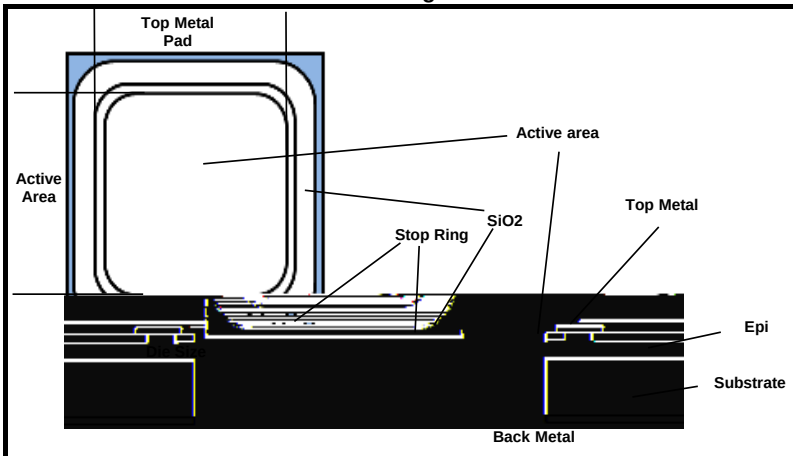
Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	600V
Average forward current	$I_{F(AV)}$	15A
(tp = 8.3 ms, halfwave, 1 cycle)	I_{FSM}	250A
Storage temperature range	T_{stg}	-40 to +150 °C
Maximum operating junction temperature	T_j	150 °C

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage I_R = 50uA	V_{BR}	680V	690V
Maximum forward voltage drop I_F 2%	V_F	0.9V	0.87V
Reverse Recovery Time I_F=0.5A, I_R=1A, I_{rr}=0.25A	Trr	500ns	440ns
Maximum reverse current $V_R = V_{RRM}$ 2%	I_R	2uA	0.05uA

Device Schematics and Outline Drawing



Die Thickness	330um
Die Size *	3000x3000um
Top Metal Pad	1878x1878um
Active Area	2252x2252um
Top Metal	Ag
Back Metal	Ag

Note: 1 *: Cutting street width is around 40um

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.